

**IN THE CLAIMS:**

Please amend the claims as follows:

Claims 1-8 (Canceled)

9. (currently amended) A heat treating method ~~for comprising the steps of distributing defects in a silicon single crystal wafer, said wafer comprising a surface region of several tens of  $\mu\text{m}$  deep and an adjacent central region, said wafer having been prepared from a perfect crystal free from grown-in defects and produced by a Czochralski method, said defects being uniformly distributed in a region consisting essentially of the central region a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method,~~ comprising by a first step of maintaining a first heat treatment temperature for an initial entry of the silicon single crystal wafer up to  $500^{\circ}\text{C}$ , and a second step of maintaining a temperature ramping rate in a temperature range from the first heat treatment temperature to a second heat treatment temperature of  $700^{\circ}\text{C}$ - $900^{\circ}\text{C}$ , said ramping rate being  $1^{\circ}\text{C}/\text{min}$  or less, ~~said first step being performed first after a wafer slicing process.~~

10. (currently amended) A heat treating method ~~for comprising the steps of distributing defects in a silicon single crystal wafer, said wafer comprising a surface region of several tens of  $\mu\text{m}$  deep and an adjacent central region, said wafer having been prepared from a perfect crystal free from grown-in defects and produced by a Czochralski method, said defects being uniformly distributed in a region consisting essentially of the central region a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method,~~ comprising by a first step of maintaining a first heat treatment temperature for an initial entry of the silicon single crystal wafer up to  $500^{\circ}\text{C}$ , and a second step of maintaining a temperature ramping rate in a temperature range from the first heat treatment temperature to a second heat treatment temperature of  $700^{\circ}\text{C}$ - $900^{\circ}\text{C}$ , said ramping rate being  $1^{\circ}\text{C}/\text{min}$  or less, so as to make uniform the distribution of an oxide precipitate density of the silicon single crystal wafer ~~in the wafer, said first step being performed first after a wafer slicing process.~~

11. (currently amended) A heat treating method ~~for comprising the steps of distributing defects in a silicon single crystal wafer, said wafer comprising a surface region of several tens of  $\mu\text{m}$  deep and an adjacent central region, said wafer having been prepared from a perfect crystal free from grown-in defects and produced by a Czochralski method, said defects being uniformly distributed in a region consisting essentially of the central region a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, comprising~~ by a first step of controlling a first heat treatment temperature for an initial entry of the silicon single crystal wafer to be a target of the heat treatment and a second step of controlling a temperature ramping rate from the heat treatment temperature at initial entry to a higher second heat treatment temperature and maintaining in a range of  $700^{\circ}\text{C}$ - $900^{\circ}\text{C}$  so as to make the distribution of an oxide precipitate density of the silicon single crystal wafer more uniform after heat treatment, ~~said first step being performed first after a wafer slicing process.~~

12. (original) The method according to Claim 9, wherein the oxygen concentration of the perfect crystal is  $13 \times 10^{17}$  atoms/ $\text{cm}^3$  or less.

13. (previously presented) A silicon single crystal wafer produced by the method according to Claim 12.

Claims 14-23 (canceled)